

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	3086	etch near2 barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 09:53
L2	2669	L1 and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 09:53
L3	1329	L1 and (copper cu)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 09:53
L4	77	L1 and (copper cu) near3 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 09:53
L5	21	L4 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 12:04
L6	43	dry adj etch adj (copper cu) and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 11:43
L7	0	"20021148952"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 11:43
L8	2	"2002148952"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 11:44

L9	2	"20020048952"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 11:58
L10	0	"20080082538"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 11:58
L11	2	"20050082538"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 12:02
L12	457	(copper cu) near2 (deposit\$3 evaporat\$3 form\$3) near2 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 12:04
L13	328	L12 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 12:05
L14	150	(copper cu) near2 (deposit\$3 evaporat\$3) near2 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 12:04
L15	109	L14 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 12:28
L16	1	@pn="5756372"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/11 12:28

S1	1	@pn="6812082"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/30 16:36
S2	386	438/625.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:25
S3	332	S2 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:26
S4	202	S3 and barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:26
S5	160	S4 and (copper cu)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:27
S6	90	S5 and mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:43
S7	27975	barrier same (copper cu)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:43
S8	4675	S7 and barrier near8 etch\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:44

S9	327	S8 and (copper cu) near5 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 15:44
S10	184	S9 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 17:08
S11	262	(cu copper) near3 through near2 mask	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 17:08
S12	93	S11 and barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 17:08
S13	43	S12 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 17:08
S43	1276	438/592.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:18
S44	1040	S43 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 13:51
S45	21	S44 and laminate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:53

S46	552	((thin adj film adj transistor) TFT) and (copper cu) same barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:53
S47	103	S46 and ((copper cu) same (etch rie))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:54
S48	136	S46 and ((copper cu) same mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:54
S49	65	S47 and ((copper cu) same mask)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 12:54
S50	32	S49 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 15:22
S51	584	etch near8 pattern near3 (cu copper) and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:13
S52	300	etch near3 pattern near3 (cu copper) and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:31
S53	0	etch near3 pattern near3 (cu copper) same gate and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:14

S54	6	etch near3 pattern near3 (cu copper) same electrode and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:15
S55	26	etch near3 pattern near3 (cu copper) same barrier and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:49
S56	2	"20020048952"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:32
S57	194	etch near3 pattern near3 barrier and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:58
S58	4	S57 and ((thin adj film adj transistor) TFT)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 15:19
S59	18	S57 and barrier same (copper cu)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 14:58
S60	685	((thin adj film adj transistor) TFT) and (source drain) near5 (dop\$3) near3 gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 15:21
S61	447	S60 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 15:23

S62	3	S61 and (cu copper) near8 gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 15:24
S63	9	S61 and (cu copper) near12 gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:16
S64	6	S63 not S62	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 15:46
S66	12042	saito.in. and hitachi.as.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:01
S67	242	S66 and (copper cu).ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:03
S68	4	S67 and transistor.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:02
S69	47	S67 and wiring.ab.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:02
S70	25	S66 and (copper cu).ab.	US-PGPUB; USPAT	OR	ON	2005/10/03 16:11
S72	38	S61 and (cu copper) same gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:16

S73	29	S72 not S63	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:23
S74	103	438/163.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:24
S75	84	S74 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/03 16:24
S76	386	438/625.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 15:11
S77	1489	438/149.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:08
S78	954	S77 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:08
S80	1256	438/151.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:17
S81	825	S80 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:20

S82	592	S81 not S78	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:08
S83	275	438/157.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:17
S84	181	S83 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:20
S85	30	S84 and (copper cu)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:21
S86	6	S85 and barrier	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:37
S87	11	(TFT (thin adj film adj transistor)) and ((cu copper) near12 gate near12 etch)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:38
S88	4	S87 and @ad<"20020920"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/05 17:38